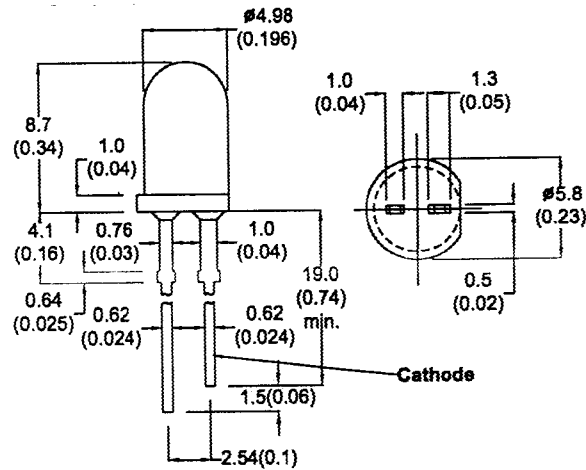


MICRO

MI51TA-2
MI51TA-3
INFRARED
EMITTING
DIODE

DESCRIPTION

MI51TA-2 & MI51TA-3 is GaAlAs infrared emitting diode molded in T-1 3/4 standard 5mm diameter clear transparent lens.



- All Dimension in mm (inch)
- No Scale
- Tol. : + / - 0.3mm

ABSOLUTE MAXIMUM RATING ($T_a=25^\circ\text{C}$)

Forward Current (Continuous)

Pulse Forward Current

Reverse Voltage (Continuous)

Power Dissipation

Operating Temperature Range

Lead Soldering Temperature (1/16" from body)

	MI51TA-2	MI51TA-3
Forward Current (Continuous)	100mA	100mA
Pulse Forward Current	1A*	1A*
Reverse Voltage (Continuous)	5V	5V
Power Dissipation	200mW	230mW
Operating Temperature Range	-25 to +85°C	
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.	

* Pulse Width = 10 μ s, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MI51TA-2	MI51TA-3	UNIT	CONDITIONS
Radiant Power Output	Min	0.6	0.8	mW	I _F =20mA
	Typ	1.0	1.5		
Forward Voltage	Typ	1.7	1.6	V	I _F =20mA
	Max	2.0	2.3		
Reverse Current	Max	100	100	μ A	V _R =5V
Peak Wavelength	Typ	770	830	nm	I _F =20mA
Spectrum Line Half Width	Typ	30	32	nm	I _F =20mA
Viewing Angle	Typ	2 θ 1/2	75	degree	I _F =20mA



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